

NTE92 (NPN) & NTE93 (PNP) Silicon Complementary Transistors Hi-Fi Power Amp, Audio Output

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	200V
Collector-Emitter Voltage, V_{CEO}	200V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	15A
Base Current, I_B	5A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	150W
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Note 1. Matched complementary pairs are available upon request (NTE93MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 200V$	-	-	0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 6V$	-	-	0.1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA$	200	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = 4V, I_C = 5A$	30	120	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, I_B = 1A$	-	3	-	V
Transistion Frequency	f_T	$V_{CE} = 12V, I_E = 0.5A$	-	20	-	MHz

